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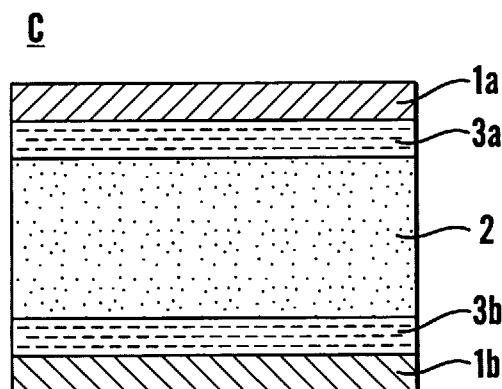
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(54) Title: A FERROELECTRIC OR ELECTRET MEMORY CIRCUIT



particularly a polymer material.

(57) Abstract: In a ferroelectric or electret memory circuit (C), particularly a ferroelectric or electret memory circuit with improved fatigue resistance, a ferroelectric or electret memory cell, preferably of polymer or oligomer memory material contacting first and second electrodes, at least one of the electrodes comprises at least one functional material capable of physical and/or chemical bulk incorporation of atomic or molecular species contained in the either electrode or the memory material and displaying a propensity for migrating in the form of mobile charged and/or neutral particles between an electrode and a memory material, something which can be detrimental to both. A functional material with the above-mentioned properties shall serve to offset any adverse effect of a migration of this kind, leading to an improvement in the fatigue resistance of the memory cell. Use in a matrix-addressable memory device where the memory cells are formed in distinct portions in a global layer of a ferroelectric or electret thin-film memory material,



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